



Description:

Designed for general-purpose amplifier and low speed switching applications.

Features:

- Collector-emitter sustaining voltage-V $_{CEO~(sus)}$ = 60V (Min.) TIP110, TIP115 Collector-emitter saturation voltage-V $_{CE~(sat)}$ = 2.5V (Max.) at I $_{C}$ = 2A Monolithic construction with built-in-base-emitter shunt resistor

Maximum Ratings

| Characteristic | Symbol | TIP110 TIP115 | Unit |
|---|-----------------------------------|------------------|-----------|
| Collector-Emitter Voltage | V _{CEO} | 60 | |
| Collector-Base Voltage | V _{CBO} | 60 V | |
| Emitter-Base Voltage | V _{EBO} | 5 | |
| Collector Current-Continuous Peak | I _C | 2 4 | А |
| Base Current | I _B | 50 | mA |
| Total Power Dissipation at T _C = 25°C Derate above 25°C | P _D | 50 0.4 | W W/°C |
| Operating and Storage Junction Temperature Range | T _J , T _{STG} | -65 to +150 | °C |

Thermal Characteristics

| Characteristic | Symbol | Max. | Unit |
|-------------------------------------|-----------------|------|------|
| Thermal Resistance Junction to Case | $R_{\theta jc}$ | 2.5 | °C/W |





Electrical Characteristics:

(T_C = 25°C unless otherwise noted)

| Characteristic | Symbol | Min. | Max. | Unit |
|---|------------------------|--------------|------------|------|
| Off Characteristics | • | • | | |
| Collector-Emitter Sustaining Voltage (1) $I_C = 30$ mA, $I_B = 0$ | V _{CEO (sus)} | 60 | - | V |
| Collector Cut off Current $V_{CE} = 30V$, $I_{B} = 0$ | I _{CEO} | - | 2 | mA |
| Collector Cut off Current $V_{CB} = 60V$, $I_E = 0$ | I _{CBO} | - | 1 | |
| Emitter Cut off Current $V_{EB} = 5V, I_{C} = 0$ | I _{EBO} | - | 2 | |
| On Characteristics (1) | | | | |
| DC Current Gain $I_C = 1A$, $V_{CE} = 4V$ $I_C = 2A$, $V_{CE} = 4V$ | h _{FE} | 1,000 500 | - | - |
| Collector-Emitter Saturation Voltage I _C = 2A, I _B = 8mA | V _{CE (sat)} | - | 2.5 | V |
| Base-Emitter On Voltage I _C = 2A, V _{CE} = 4V | V _{BE (on)} | - | 2.8 | |
| Dynamic Characteristics | | | | |
| Small-Signal Current Gain $I_C = 0.75A$, $V_{CE} = 10V$, $f = 1MHz$ | h _{fe} | 25 | | - |
| Output Capacitance V _{CB} = 10V, I _E = 0, f = 0.1MHz TIP115 | C _{ob} | - | 250 150 | pF |

(1) Pulse Test: Pulse Width = 300µs, Duty Cycle ≤2%.

TIP115

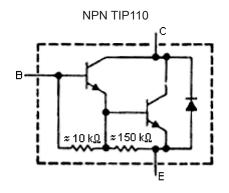
Figure - 1 Power Derating 50 P_D, Power Dissipation (Watts) 45 40 35 30 25 20 15 10 5 0 125 150 T_C, Temperature (°C)

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Internal Schematic Diagram



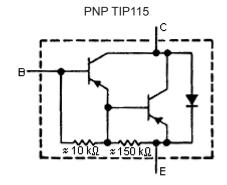


Figure - 2 Switching Time

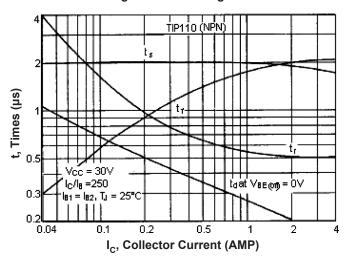


Figure - 3 Switching Time

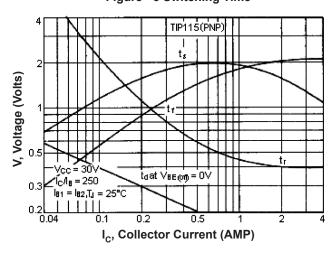


Figure - 4 Capacitances

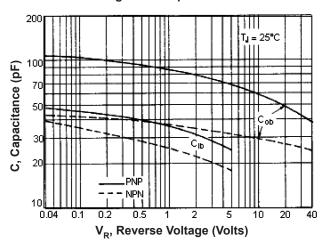
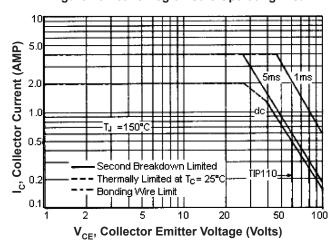


Figure - 5 Active Region Safe Operating Area

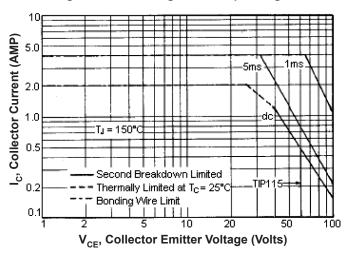


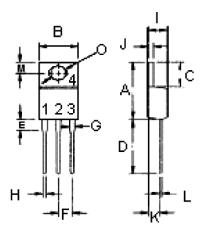
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Figure - 6 Active Region Safe Operating Area





Pin Configuration:

- 1. Base
- 2. Collector
- 3. Emitter
- 4. Collector(Case)

There are two limitation on the power handling ability of a transistor: average junction temperature and second breakdown safe operating area curves indicate I_C - V_{CE} limits of the transistor that must be observed for reliable operation i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure - 5 and 6 is base on $T_{J (PK)} = 150 ^{\circ} C$; T_{C} is variable depending on power level. Second breakdown pulse limits are valid for duty cycles to 10% provided $T_{J (PK)} \leq 150 ^{\circ} C$, At high case temperatures, thermal limitation will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

| Dimensions | Min. | Max. |
|------------|-------|-------|
| А | 14.68 | 15.31 |
| В | 9.78 | 10.42 |
| С | 5.01 | 6.52 |
| D | 13.06 | 14.62 |
| E | 3.57 | 4.07 |
| F | 2.42 | 3.66 |
| G | 1.12 | 1.36 |
| Н | 0.72 | 0.96 |
| I | 4.22 | 4.98 |
| J | 1.14 | 1.38 |
| K | 2.2 | 2.97 |
| L | 0.33 | 0.55 |
| M | 2.48 | 2.98 |
| 0 | 3.7 | 3.9 |

Dimensions: Millimetres

Part Number Table

| Description | Part Number | |
|------------------------------------|-------------|--|
| Darlington Transistor, NPN, TO-220 | TIP110 | |
| Darlington Transistor, PNP, TO-220 | TIP115 | |

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